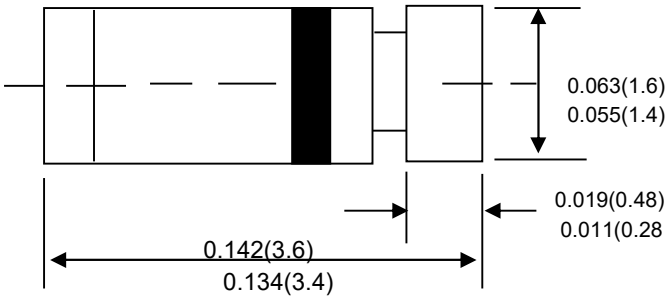
SWITCHING DIODE

Parameter	Value	Unit
V_R	75	V
I_O	150	mA



inch(mm)

LL-34(SOD-80)

Features

- Silicon epitaxial diode
- 500mW power dissipation
- High speed switching diode

Absolute Maximum Ratings and Characteristics (at Ta = 25℃ unless otherwise specified)

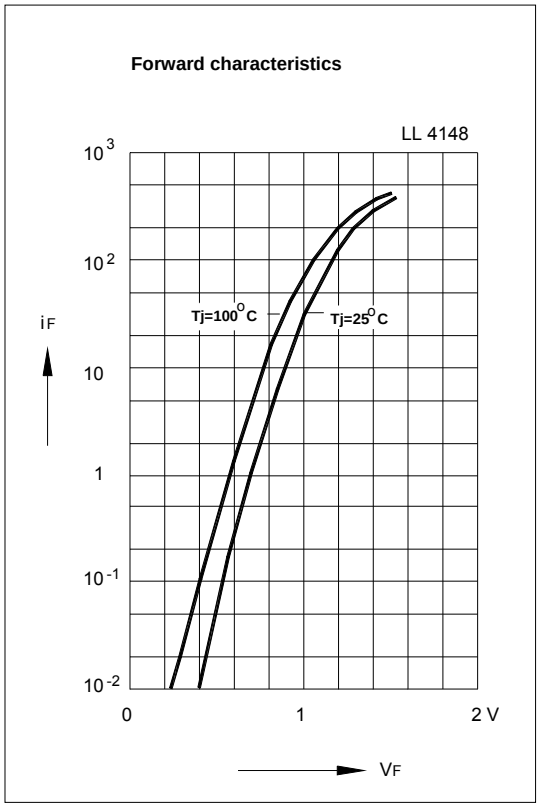
Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	75	V
Peak Reverse Voltage	V_{RM}	100	V
Average Rectified Forward Current	I_O	150	mA
Forward Surge Current	I_{FSM}	500	mA
Power Dissipation	P_{tot}	500[1)]	mW
Junction Temperature	T_J	175	℃
Storage Temperature Range	T_{STG}	- 65 to + 175	℃

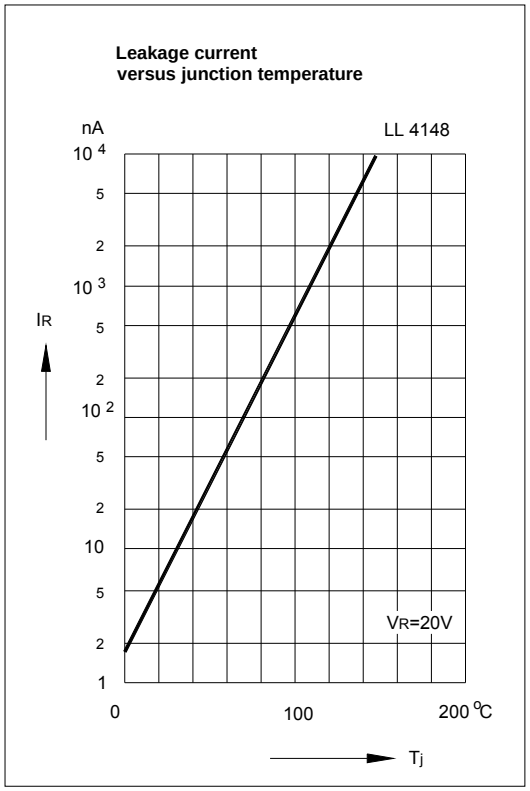
Notes:
1) Valid provided that leads at a distance of 8mm from case are kept at ambient temperature.

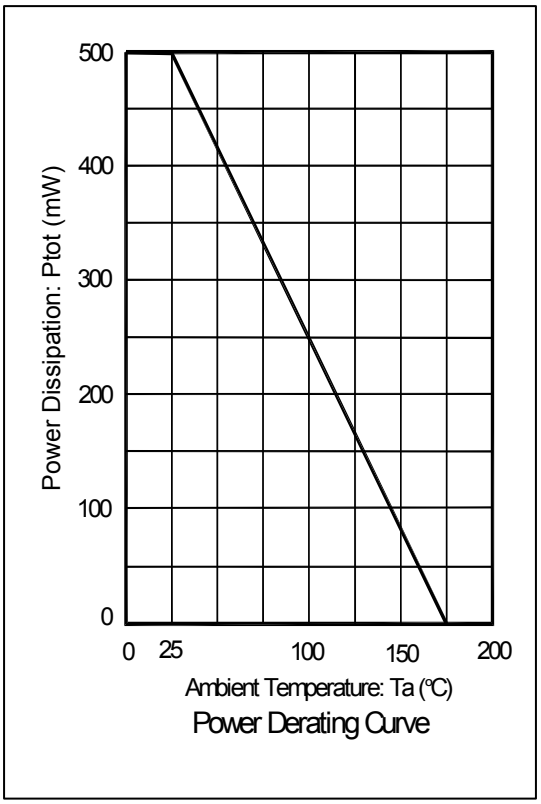
Characteristics (at TJ = 25℃ unless otherwise specified)

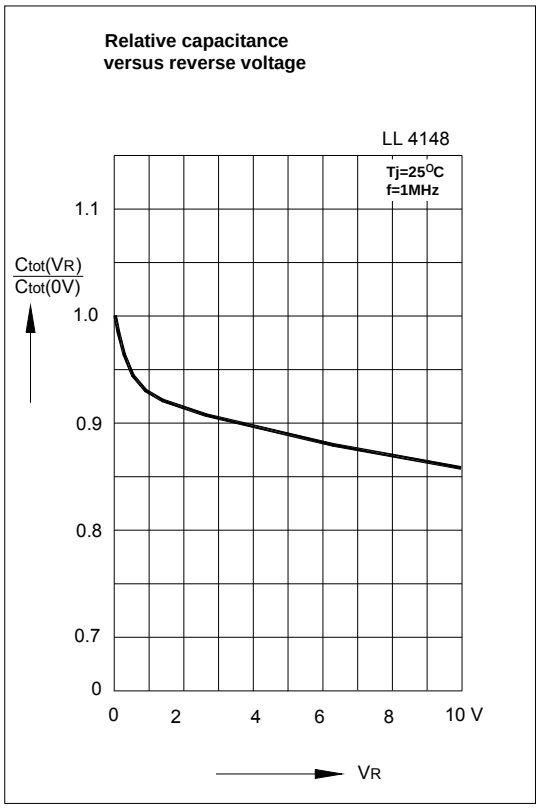
Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at I_F=10mA	V_F	-	1	V
Leakage Current at V_R=20V at V_R=75V at V_R=20V, Tj=150℃	 I_R I_R I_R	 - - -	 25 5 50	 nA μA μA
Voltage Rise when Switching ON tested with 50mA Forward Pulses, tp=0.1s, Rise Time < 30ns, f =5 to100KHz	V_{fr}	-	2.5	V
Capacitance at V_R=0, f =1MHz	C_{tot}	-	4	pF
Reverse Recovery Time at I_F=10mA to I_R=1mA, V_R=6V, R_L=100Ω	trr	-	4	ns
Thermal Resistance Junction to Ambient	RthA	-	350[1)]	K/W
Rectification Efficiency at f =100MHz, V_{RF}=2V	nV	0.45	-	-

Typical characteristics









***Important Usage Information and Disclaimer**

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